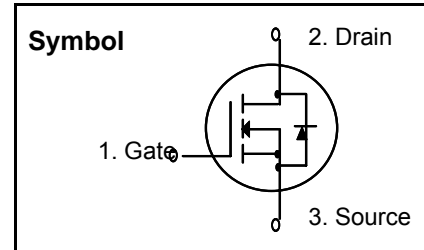


## N-Channel MOSFET

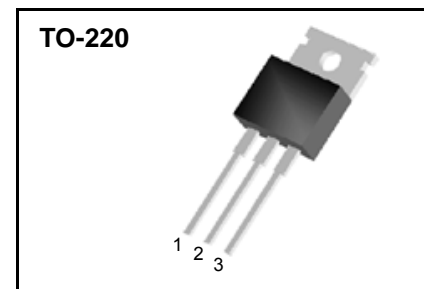
### Features

- $R_{DS(on)}$  (Max 0.55  $\Omega$ )@ $V_{GS}=10V$
- Gate Charge (Typical 38nC)
- Improved dv/dt Capability, High Ruggedness
- 100% Avalanche Tested
- Maximum Junction Temperature Range (150°C)



### General Description

This Power MOSFET is produced using Wisdom's advanced planar stripe, DMOS technology. This latest technology has been especially designed to minimize on-state resistance, have a high rugged avalanche characteristics. These devices are well suited for high efficiency switching DC/DC converters, switch mode power supply, DC-AC converters for uninterrupted power supply, motor control.



### Absolute Maximum Ratings

Symbol	Parameter	Value	Units
$V_{DSS}$	Drain to Source Voltage	400	V
$I_D$	Continuous Drain Current(@ $T_C = 25^\circ C$ )	10	A
	Continuous Drain Current(@ $T_C = 100^\circ C$ )	6.3	A
$I_{DM}$	Drain Current Pulsed (Note 1)	40	A
$V_{GS}$	Gate to Source Voltage	$\pm 25$	V
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	450	mJ
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	13.4	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5	V/ns
$P_D$	Total Power Dissipation(@ $T_C = 25^\circ C$ )	134	W
	Derating Factor above 25 °C	1.08	W/°C
$T_{STG}, T_J$	Operating Junction Temperature & Storage Temperature	- 55 ~ 150	°C
$T_L$	Maximum Lead Temperature for soldering purpose, 1/8 from Case for 5 seconds.	300	°C

### Thermal Characteristics

Symbol	Parameter	Value			Units
		Min.	Typ.	Max.	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	-	-	0.93	°C/W
$R_{\theta CS}$	Thermal Resistance, Case to Sink	-	0.5	-	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	-	-	62.5	°C/W

## Electrical Characteristics

$T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	400	--	--	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	0.50	--	$\text{V}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	$\mu\text{A}$
		$V_{DS} = 320\text{ V}, T_C = 125^\circ\text{C}$	--	--	10	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 25\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -25\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 5.0\text{ A}$	--	0.44	0.55	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 5.0\text{ A}$ (Note 4)	--	9.0	--	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	1570	2040	pF
$C_{oss}$	Output Capacitance		--	150	195	pF
$C_{rss}$	Reverse Transfer Capacitance		--	15	20	pF

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 200\text{ V}, I_D = 10.0\text{ A},$ $R_G = 25\ \Omega$	--	25	60	ns	
$t_r$	Turn-On Rise Time		--	75	160	ns	
$t_{d(off)}$	Turn-Off Delay Time		(Note 4, 5)	--	115	240	ns
$t_f$	Turn-Off Fall Time		(Note 4, 5)	--	70	150	ns
$Q_g$	Total Gate Charge		$V_{DS} = 320\text{ V}, I_D = 10.0\text{ A},$ $V_{GS} = 10\text{ V}$	--	38	50	nC
$Q_{gs}$	Gate-Source Charge	(Note 4, 5)	--	8	--	nC	
$Q_{gd}$	Gate-Drain Charge		--	13	--	nC	

### Drain-Source Diode Characteristics and Maximum Ratings

$I_S$	Maximum Continuous Drain-Source Diode Forward Current	--	--	10	A	
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current	--	--	40	A	
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 10.0\text{ A}$	--	--	1.5	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 10.0\text{ A},$ $dI_F / dt = 100\text{ A}/\mu\text{s}$	--	225	--	ns
$Q_{rr}$	Reverse Recovery Charge	(Note 4)	--	1.59	--	$\mu\text{C}$

#### Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2.  $L = 7.9\text{ mH}, I_{AS} = 10.0\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 10.0\text{ A}, dI/dt \leq 300\ \mu\text{A}/\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width  $\leq 300\ \mu\text{s}$ , Duty cycle  $\leq 2\%$
5. Essentially independent of operating temperature

# Typical Characteristics

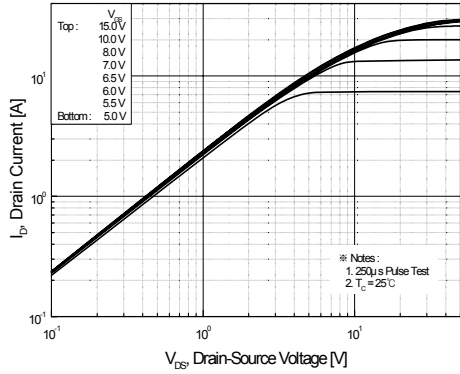


Figure 1. On-Region Characteristics

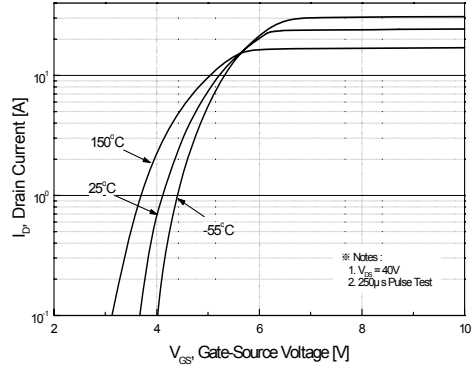


Figure 2. Transfer Characteristics

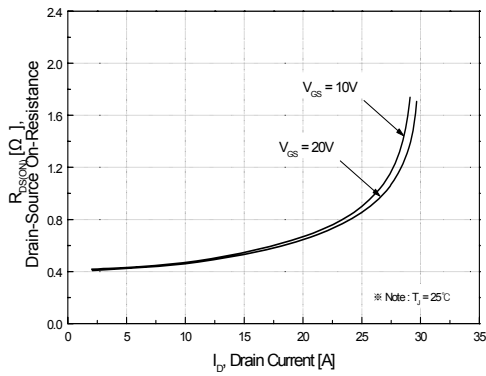


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

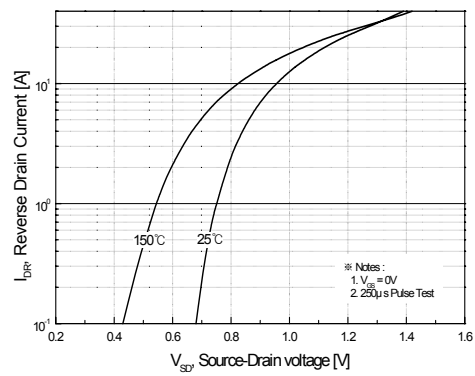


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

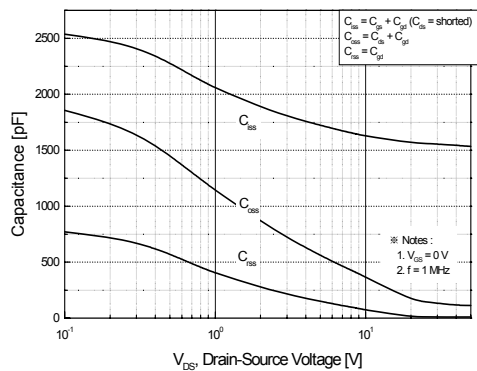


Figure 5. Capacitance Characteristics

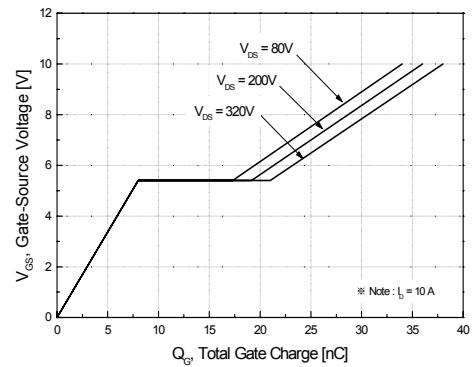
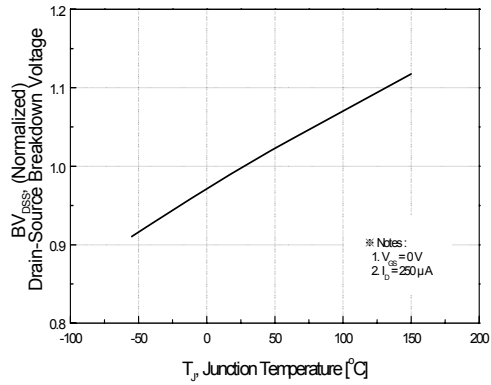
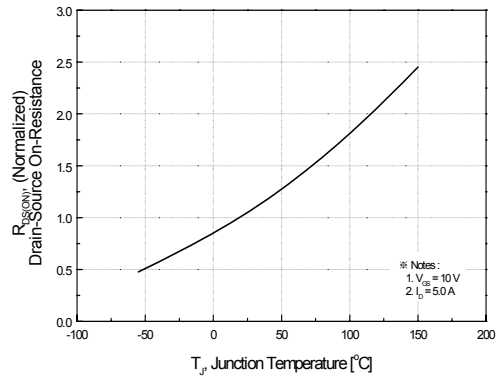


Figure 6. Gate Charge Characteristics

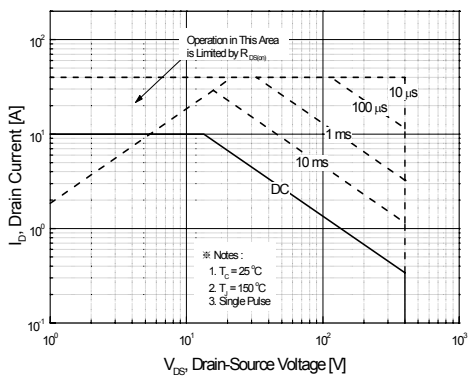
## Typical Characteristics (Continued)



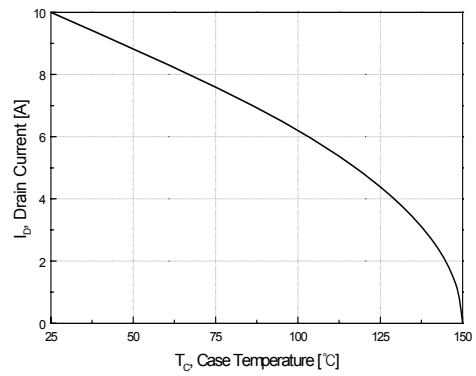
**Figure 7. Breakdown Voltage Variation vs Temperature**



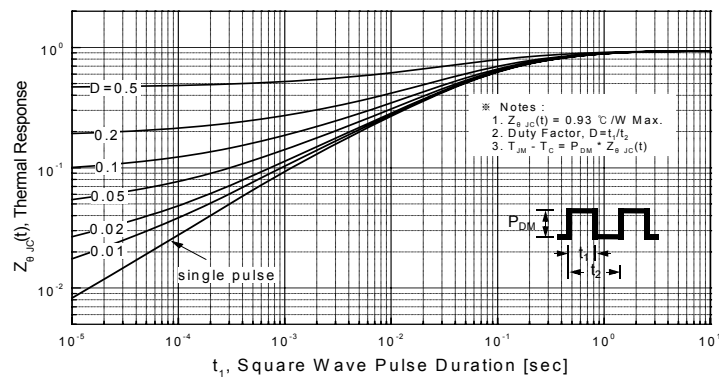
**Figure 8. On-Resistance Variation vs Temperature**



**Figure 9. Maximum Safe Operating Area**

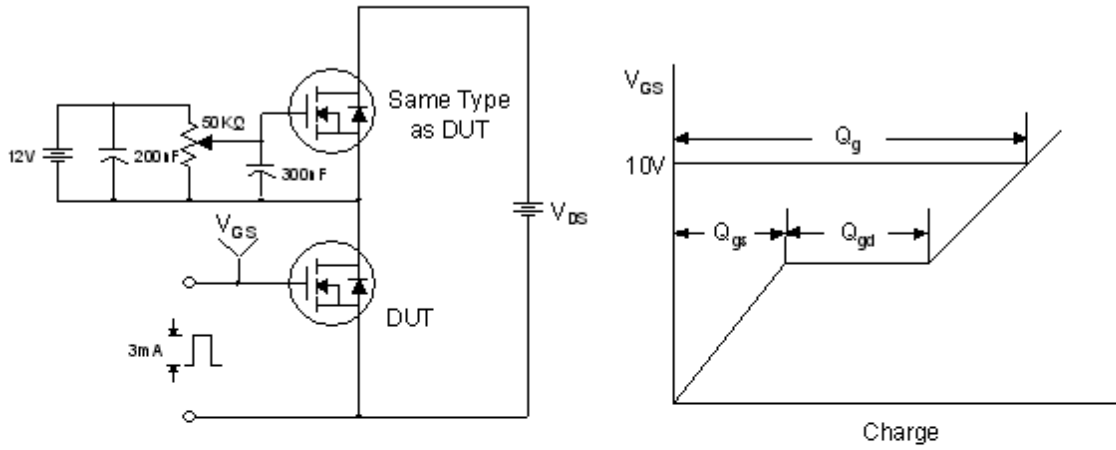


**Figure 10. Maximum Drain Current vs Case Temperature**

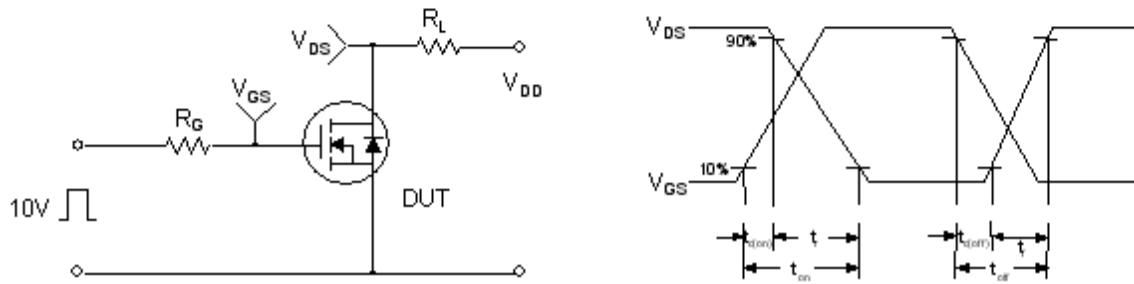


**Figure 11. Transient Thermal Response Curve**

### Gate Charge Test Circuit & Waveform



### Resistive Switching Test Circuit & Waveforms



### Unclamped Inductive Switching Test Circuit & Waveforms

